



University of Tehran

School of Electrical and Computer Engineering

Course:	Transport Phenomena in Semiconductors		
Course type:	Elective	EE	Credit: 3
Level:	Graduate		
Co-requisite(s):			
Prerequisite(s):	Physical Electronics, Quantum Mechanics, Solid State Physics		
Prerequisite by topic:	Being familiar with the concepts of solid state physics and semiconductor devices		
Textbook(s):	<p>[1] M. Lundstrom, "<i>Fundamentals of Carrier Transport</i>," Cambridge University Press; 2nd edition (2000).</p> <p>[2] C. Jacoboni, "<i>Theory of Electron Transport in Semiconductors</i>," Springer, (2010).</p> <p>[3] S. Datta, "<i>Quantum Phenomena</i>," (Modular Series on Solid State Devices, Vol 8), Addison-Wesley (1989).</p> <p>[4] K. Tomizawa, "<i>Numerical Simulation Of Submicron Semiconductor Devices</i>," Artech House (1993).</p>		
Coordinator:	Mahdi Pourfath		
Goals:	<p>Introducing the students with the following topics:</p> <ul style="list-style-type: none"> – Different scattering mechanisms in semiconductors – Evaluating scattering rates for 1D, 2D, and 3D structures – Semi-classical Boltzmann equation and its numerical solutions – Low field and high field transport – Transport in Mesoscopic systems and quantum transport 		
Outcome:	<p>Upon successful completion of the course, students will be able to:</p> <ul style="list-style-type: none"> – Obtain a deeper insight into the operation of semiconductor devices – Evaluate scattering rates in 1D, 2D, and 3D structures and obtain the mobility and conductivity of such structures – Solve the Boltzmann equation using numerical methods, such as the method of moments, spherical harmonics, and Monte Carlo for analyzing semiconductor devices 		

Topics:	<p>Review of Semiconductor Physics: Electrons in periodic potential, electronic bandstructure, effective mass, density of states in 1D, 2D, and 3D structures, lattice vibrations and phonons</p> <p>Carrier Scattering: Fermi golden rule, perturbation potential, scattering with acoustic, optical, and polar optical phonons, interaction with ionized impurities and surface roughness, major sources of scattering in Si and GaAs</p> <p>Boltzmann Equation: Concepts of statistical mechanics, distribution function in equilibrium, Boltzmann equations, collision integral, analytical solution of the Boltzmann equation for some simple problems, Numerical solution of the Boltzmann equation</p> <p>Low Field Transport: Linear response theory, transport coefficients, Hall effect, thermoelectric effects, mobility at low fields</p> <p>Method of Moments: Balance equations, moments of the distribution function, Hydrodynamic model, Drift-Diffusion equation</p> <p>Monte Carlo: Statistical methods for solving differential equations, free flight time, selection of the scattering mechanism, single particle and ensemble particle Monte Carlo</p> <p>High Field Transport: Hot electrons, velocity saturation, energy relaxation time, high field transport in Si and GaAs</p> <p>Advanced Topics: semi-classical ballistic transport, transport in mesoscopic systems, quantum transport, transmission probability, scattering matrices, Landauer-Buttiker formula</p>								
Grading:	<table> <tr> <td>Assignments:</td> <td>5%</td> </tr> <tr> <td>Projects:</td> <td>15%</td> </tr> <tr> <td>Midterm exams:</td> <td>40%</td> </tr> <tr> <td>Final exam:</td> <td>40%</td> </tr> </table>	Assignments:	5%	Projects:	15%	Midterm exams:	40%	Final exam:	40%
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Further readings:									
Prepared by:	Mahdi Pourfath								
Date:	Nov. 2016								